

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: IKEMASU et al.

Serial Number: 10 050,169

Filed: January 18, 2002

For: HIGHLY INTEGRATED AND RELIABLE DRAM
AND ITS MANUFACTURE

Prior Group Art Unit: 2814

Prior Examiner: WEISS

AMENDMENT TRANSMITTAL

Commissioner for Patents
Washington, D.C. 20231

Sir:

Transmitted herewith is an Amendment in the above-identified application.

The fee has been calculated as shown below:

	CLAIMS AS AMENDED						
	Claims Remaining After Amendment	Highest Number Previously Paid For		Present Extra	Small Entity	Large Entity	Additional Fee
Total Claims	37	23	=	14	X \$9	X \$18	\$252.00
Independent Claims	3	0	=	0	X \$42	X \$84	0
## First Presentation of Multiple Dependent Claims					\$140	280	
TOTAL FEES ENCLOSED:							\$252.00

RECEIVED
TECHNICAL CENTER
FEB 27 2002

X Enclosed please find our check in the amount of **\$252.00** for the additional claims fee in connection with this amendment. The Commissioner is hereby authorized to charge payment for any additional fees associated with this communication or credit any overpayment to Deposit Account No. 01-2340. Two duplicates of this sheet are attached.

Respectfully submitted,

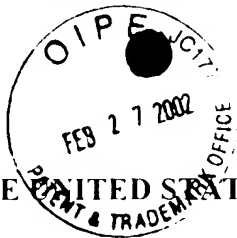
ARMSTRONG, WESTERMAN & HATTORI, LLP

A handwritten signature in black ink, appearing to read 'Donald W. Hanson', with a long horizontal flourish extending to the right.

Donald W. Hanson
Attorney for Applicants
Reg. No. 27,133

Atty. Docket No. **970607B**
1725 K Street, N.W., Suite 1000
Washington, DC 20006
Tel: (202) 659-2930
Fax: (202) 887-0357
SGA/arf

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re the Application of: IKEMASU et al.

Serial Number: 10 050,169

Filed: January 18, 2002

Prior Group Art Unit: 2814

For: HIGHLY INTEGRATED AND RELIABLE DRAM
AND ITS MANUFACTURE

Prior Examiner: WEISS

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 27, 2002

Sir:

Prior to examination of the above-identified divisional application, please amend the same as follows:

IN THE CLAIMS:

Please amend Claim 1, as follows:

1. (Amended) A semiconductor device comprising:
 - a semiconductor substrate;
 - a first insulating film formed over said semiconductor substrate;
 - a capacitor formed over said first insulating film, and having one electrode which includes an extension extending over said first insulating film;
 - a second insulating film formed over said first insulating film;
 - a first contact hole formed through said second insulating film and said extension of the one electrode; and
 - a first conductor pattern burying said first contact hole.

RECEIVED
FEB 27 2002
TECHNOLOGY CENTER
FEB 22 2002
RECEIVED